

HERB

High Efficiency Rectifier Bridges 10 Amp., 50-200V

Designed for High Frequency Switching Power Supply Applications

Extremely Low Leakage at High Temperatures

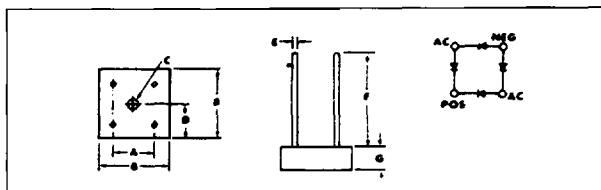
High Surge Capability

Low Cost Epoxy Encapsulation

Glass Passivation

Metal Mounting Pad to Facilitate Heatsinking

LTR.	INCHES	MILLIMETERS
A	.411-.441	10.44-11.20
B	.590-.610	14.99-15.49
C	.137-.167 Dia.	3.48-4.24 Dia.
D	.295-.305	7.49-7.75
E	.037-.043 Dia.	.94-1.09 Dia.
F	1.0 Min.	25.4 Min.
G	.195-.205	4.95-5.21



MAXIMUM RATINGS (At 25°C unless otherwise noted)

RATINGS	SYMBOL	VJ048H	VJ148H	VJ248H
DC Blocking Voltage	V_{RM}	50V	100V	200V
Working Peak Reverse Voltage	V_{RWM}			
Peak Repetitive Reverse Voltage	V_{RRM}			
RMS Reverse Voltage	$V_{R(RMS)}$	35V	70V	140V
Peak Surge Current, 1/2 Cycle at 60 Hz, (non-rep) $T_{HS} = 80^{\circ}C$	I_{FSM}	150 Amps		
Average Rectified Output Current	I_o	10 Amp @ $T_c = 80^{\circ}C$		
Junction Operating and Storage Temperature		- 50 to + 150°C		
Maximum Soldering Temperature & Time		10 Sec. at 265°C		

ELECTRICAL CHARACTERISTICS (At $T_A = 25^{\circ}C$ unless otherwise noted)

Maximum Instantaneous Forward Voltage Drop per Diode at 10 Amp.	V_{FM}	1.0 V @ $T_j = 25^{\circ}C$ 0.92 V @ $T_j = 100^{\circ}C$
Maximum Reverse Recovery Time $I_F = .5A, I_R = 1A, I_{RR} = .25A$	t_r	30nS
Maximum Reverse Current at Rated V_{RM}	I_{RM}	5.0 μ A @ $T_j = 25^{\circ}C$ 150 μ A @ $T_j = 150^{\circ}C$
Typical Junction Capacitance (1MHz, $V_R = -10V$) per individual diode	C_j	75 pf
Insulation Strength From Circuit to Case (min.)		2000VDC

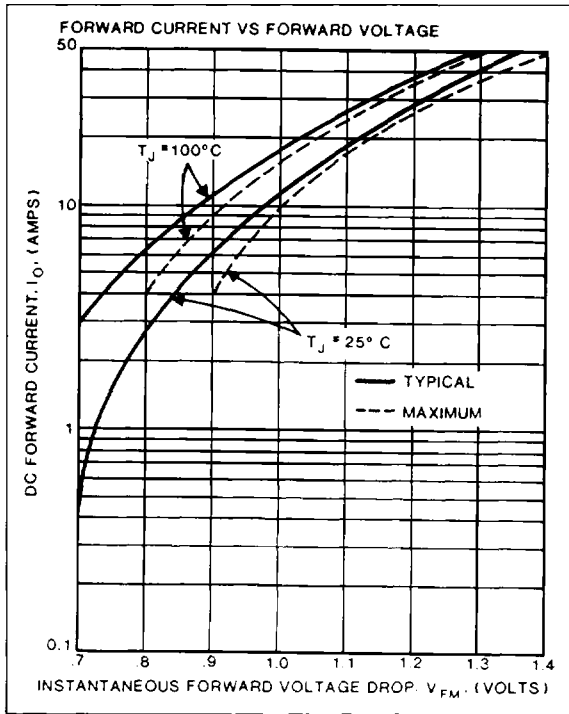


FIGURE 1

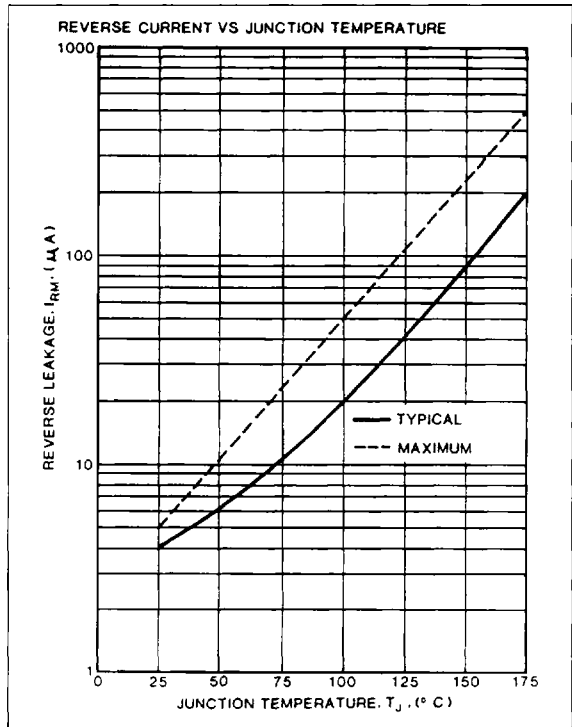


FIGURE 2

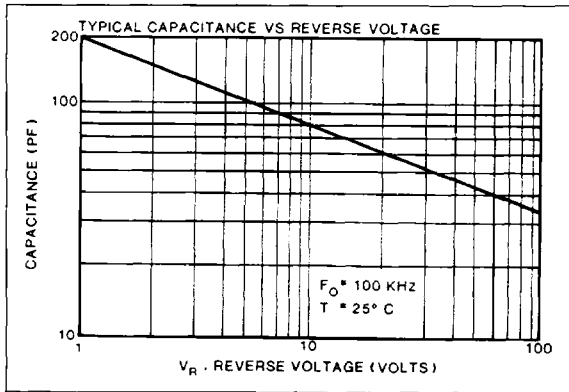


FIGURE 3

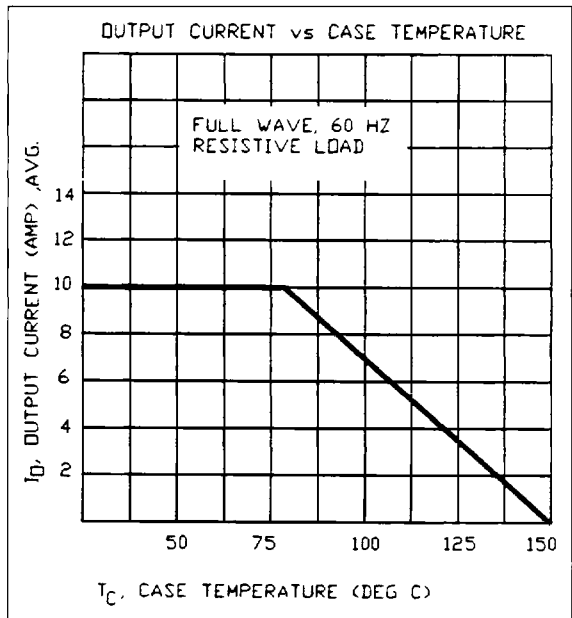


FIGURE 4